

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>	Complete if Known	
	Application Number	10/081,818
	Filing Date	February 20, 2002
	First Named Inventor	Eldridge, Jerome
	Group Art Unit	2818
	Examiner Name	Ho, Tu-Tu
Sheet 1 of 1	Attorney Docket No: 1303.045US1	

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Examiner Initials *	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T *
TH		"ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS", <u>US Application Serial No 10/379470 (1303.090US1) filed March 4, 2003,</u>		
↓		"COBALT TITANIUM OXIDE DIELECTRIC FILMS", <u>US Application Serial No. 11/216958 (Attorney Docket No 1303.150US1), filed August 31, 2005,</u>		
		"MAGNESIUM TITANIUM OXIDE FILMS", <u>US Application Serial No 11/89075 (Attorney Docket No. 1303.148US1) filed July 25, 2005,</u>		
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/Tu Tu Ho/ (12/15/2006)

DATE CONSIDERED 12/15/2006

PTO/SB/06A(10-01)

Approved for use through 10/31/2002. OMB 051-0031  
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First Named Inventor Eldridge, Jerome

Group Art Unit 2818

Examiner Name Ho, Tu-Tu

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/Tu Tu Ho/ (02/28/2007)

DATE CONSIDERED

02/28/2007

Substitute Disclosure Statement Form (PTO-1449)

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Sheet 1 of 1

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T <sup>2</sup>
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TH		AHN, KIE Y., et al., "MAGNESIUM TITANIUM OXIDE FILMS", U.S. Application Serial No. 11/189,075, filed July 25, 2005 (Attorney Docket 1303.148US1)	
TH		HODGES, D. A., et al., "Analysis and Design of Digital Integrated Circuits", McGraw-Hill Book Company, 2nd Edition, (1988),394-396	
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EXAMINER

/Tu Tu Ho/ (02/28/2007)

DATE CONSIDERED

02/28/2007

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached



N 10/081,818

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jerome M. Eldridge et al. Examiner: Tu-Tu V. Ho  
Serial No.: 10/081,818 Group Art Unit: 2818  
Filed: February 20, 2002 Docket: 1303.045US1  
Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW  
ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATIONS

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Noted, Feb. 07 Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

	<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
TH	11508090	August 22, 2006	1303.024US4	FLOATING GATE STRUCTURES
TH	11590363	October 31, 2006	1303.014US3	FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
TH	11565826	December 1, 2006	1303.141US2	HAFNIUM TITANIUM OXIDE FILMS
TH	11619080	January 2, 2007	1303.027US4	IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,

JEROME M. ELDRIDGE ET AL.

By Applicants' Representatives,

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Date 8 Feb '07

By [Signature]  
Timothy B. Clise  
Reg. No. 40,957

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